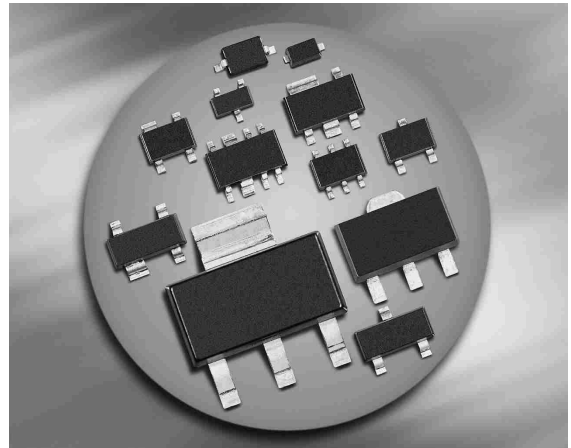


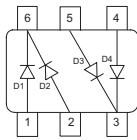
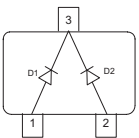
**Silicon Switching Diode**

- For high-speed switching applications
- Common cathode configuration



**BAV70**  
**BAV70F**  
**BAV70L3**  
**BAV70T**  
**BAV70W**

**BAV70S**  
**BAV70U**



Type	Package	Configuration	Marking
BAV70	SOT23	common cathode	A4s
BAV70F*	TSFP-3	common cathode	A4s
BAV70L3 **	TSLP-3-1	common cathode, leadless	A4
BAV70S	SOT363	double common cathode	A4s
BAV70T	SC75	common cathode	A4s
BAV70U	SC74	double common cathode	A4s
BAV70W	SOT323	common cathode	A4s

\* Preliminary Data

\*\* Target Data

**Maximum Ratings at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	80	V
Peak reverse voltage	$V_{RM}$	85	
Forward current	$I_F$	200	mA
Non-repetitive peak surge forward current	$I_{FSM}$		A
$t = 1 \mu\text{s}$		4.5	
$t = 1 \text{ ms}$		1	
$t = 1 \text{ s single}$		0.5	
$t = 1 \text{ s double}$		0.75	
Total power dissipation	$P_{tot}$		mW
BAV70, $T_S \leq 33^\circ\text{C}$		250	
BAV70F, $T_S \leq \text{tdb}$		250	
BAV70L3, $T_S \leq \text{tdb}$		250	
BAV70S, $T_S \leq 85^\circ\text{C}$		250	
BAV70T, $T_S \leq 73^\circ\text{C}$		250	
BAV70U, $T_S \leq 90^\circ\text{C}$		250	
BAV70W, $T_S \leq 103^\circ\text{C}$		250	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
BAV70		$\leq 460$	
BAV70F		$\leq \text{tdb}$	
BAV70L3		$\leq \text{tdb}$	
BAV70S		$\leq 260$	
BAV70T		$\leq 310$	
BAV70U		$\leq 240$	
BAV70W		$\leq 190$	

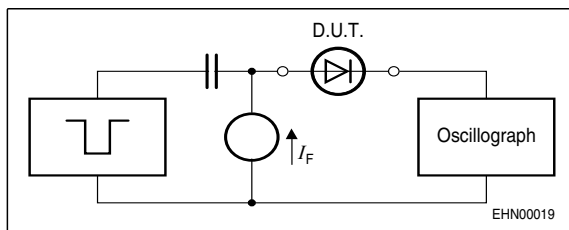
<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	85	-	-	V
Reverse current $V_R = 70 \text{ V}$ $V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$ $V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$	$I_R$	-	-	0.15 30 50	$\mu\text{A}$
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 150 \text{ mA}$	$V_F$	-	-	715 855 1000 1200 1250	mV

**AC Characteristics**

Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	$C_T$	-	-	1.5	pF
Reverse recovery time $I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$ , measured at $I_R = 1 \text{ mA}$ , $R_L = 100 \Omega$	$t_{rr}$	-	-	4	ns

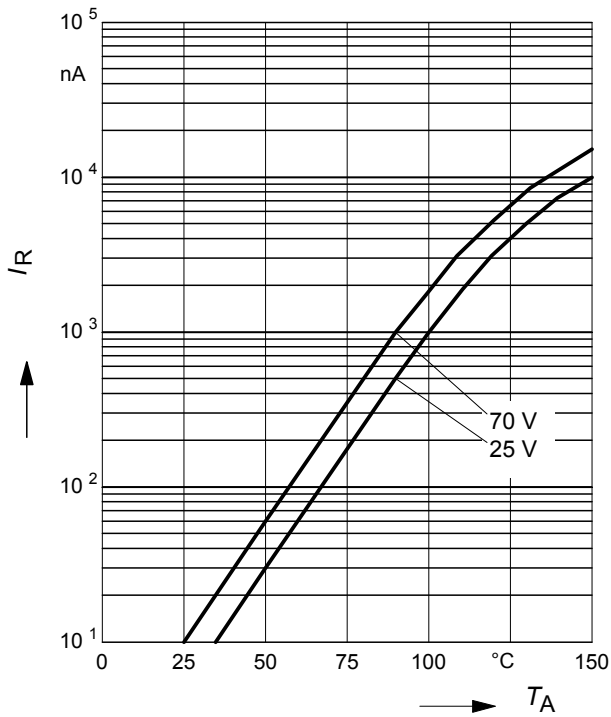
**Test circuit for reverse recovery time**


Pulse generator:  $t_p = 100\text{ns}$ ,  $D = 0.05$ ,  $t_r = 0.6\text{ns}$ ,  
 $R_i = 50\Omega$

Oscilloscope:  $R = 50\Omega$ ,  $t_r = 0.35\text{ns}$ ,  $C = 0.05\text{pF}$

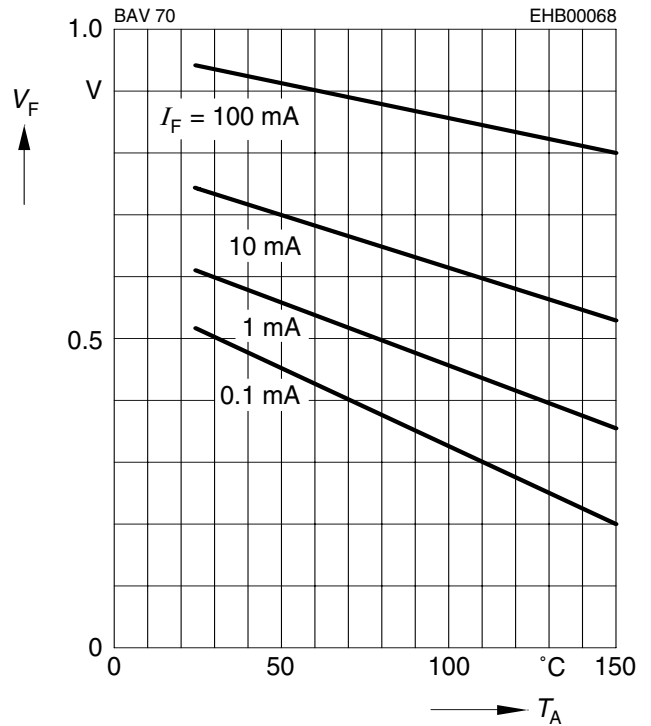
**Reverse current  $I_R = f(T_A)$**

$V_R =$  Parameter



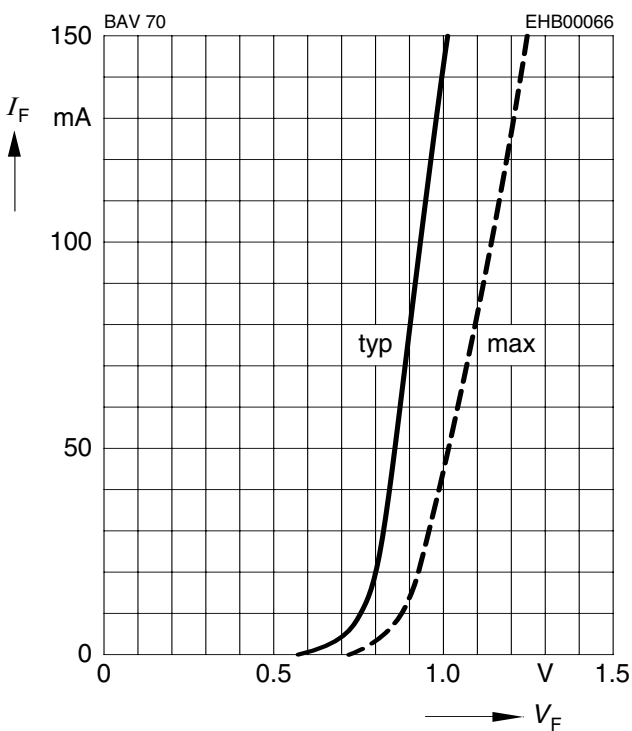
**Forward Voltage  $V_F = f(T_A)$**

$I_F =$  Parameter



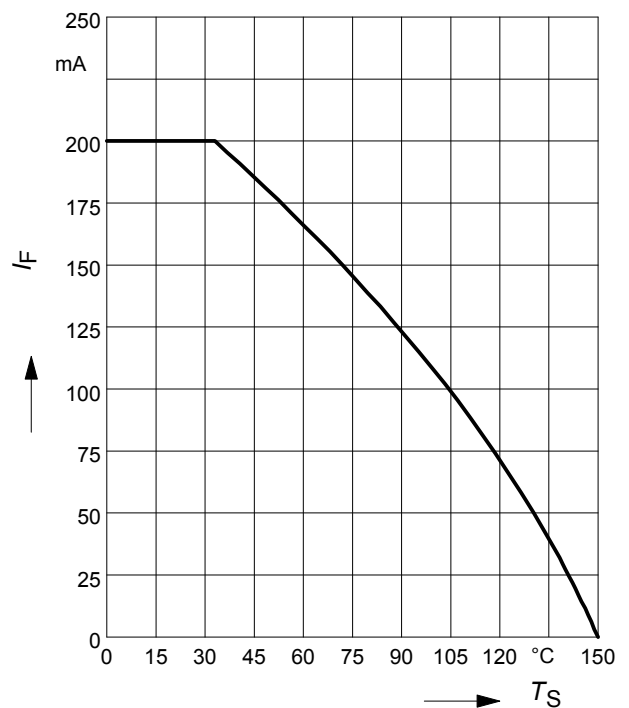
**Forward current  $I_F = f(V_F)$**

$T_A = 25^\circ\text{C}$



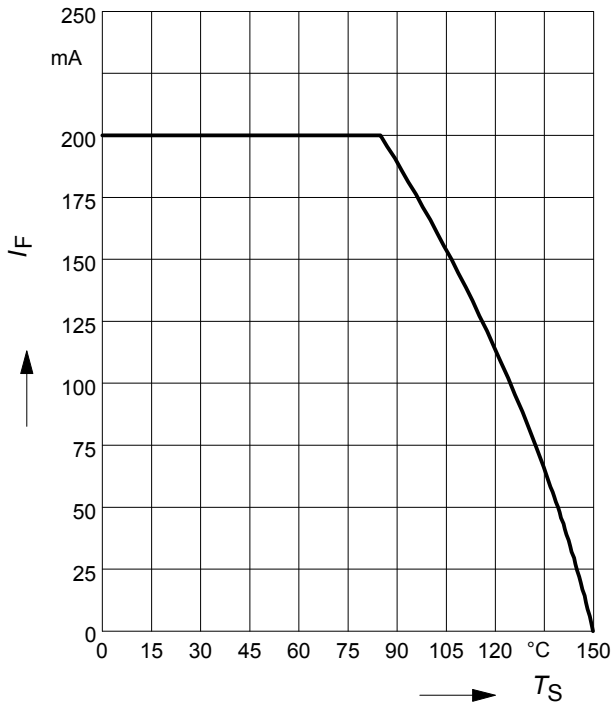
**Forward current  $I_F = f(T_S)$**

BAV70



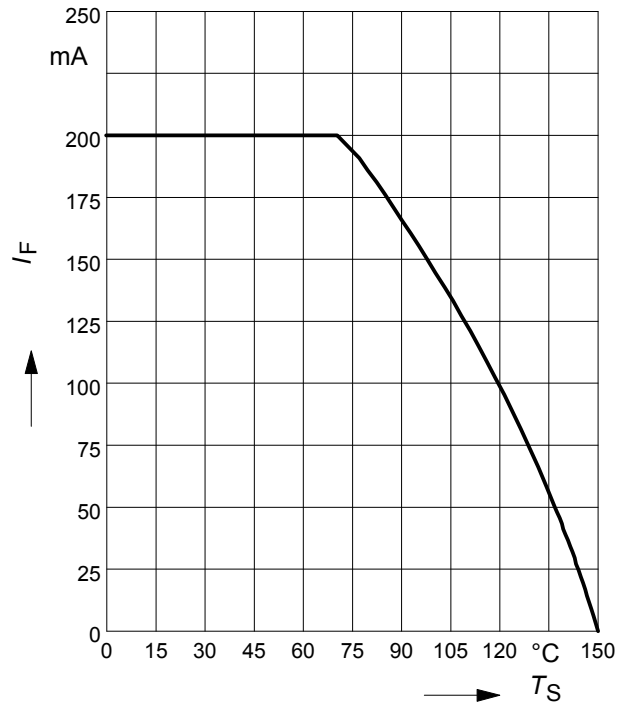
Forward current  $I_F = f(T_S)$

BAV70S



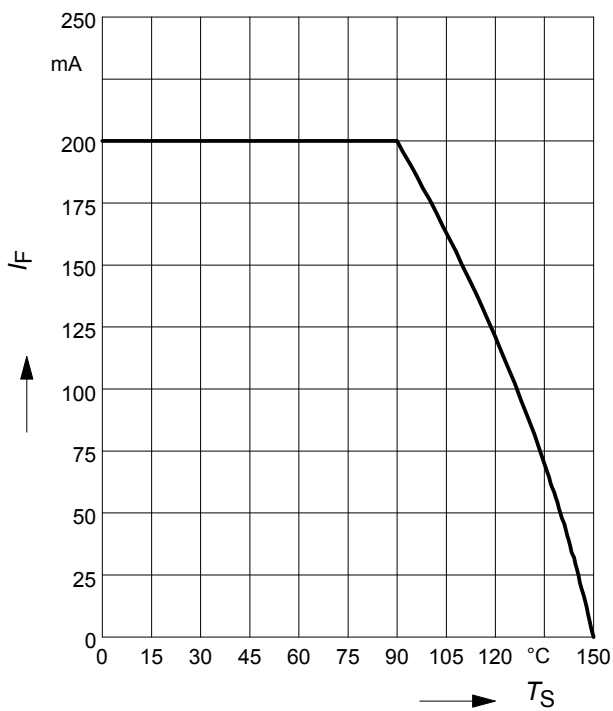
Forward current  $I_F = f(T_S)$

BAV70T



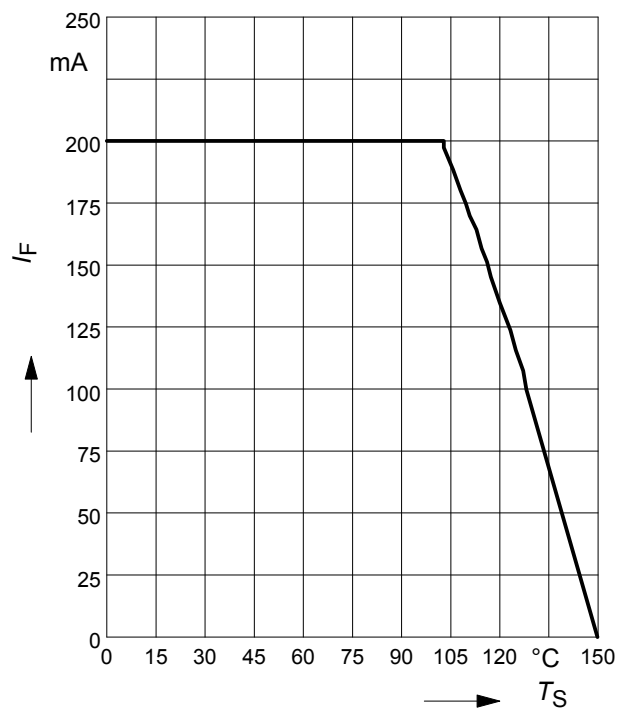
Forward current  $I_F = f(T_S)$

BAV70U



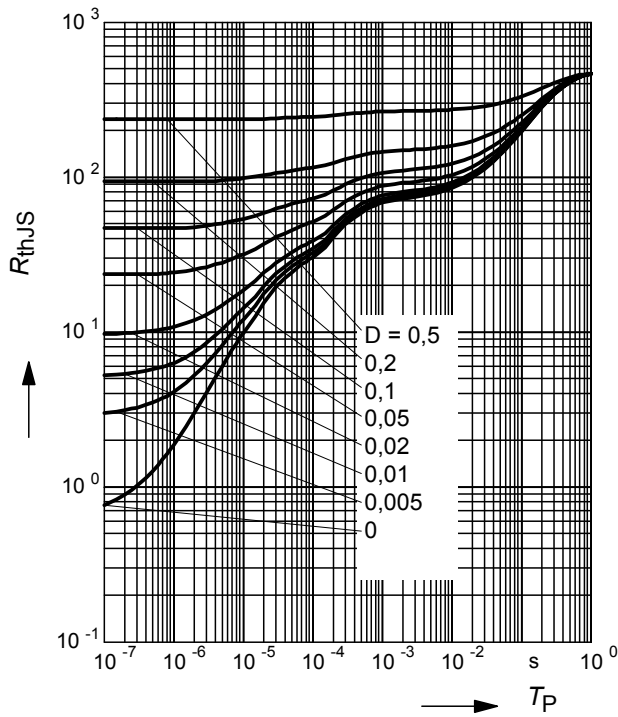
Forward current  $I_F = f(T_S)$

BAV70W



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

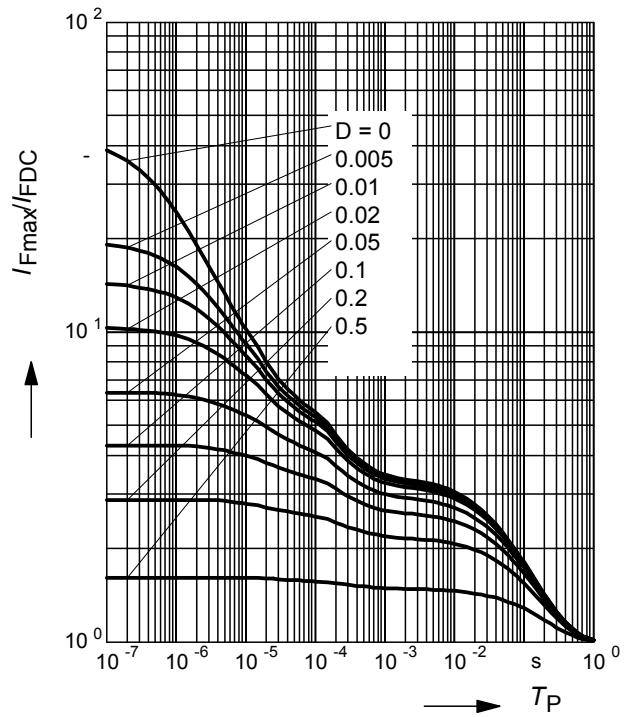
BAV70



**Permissible Pulse Load**

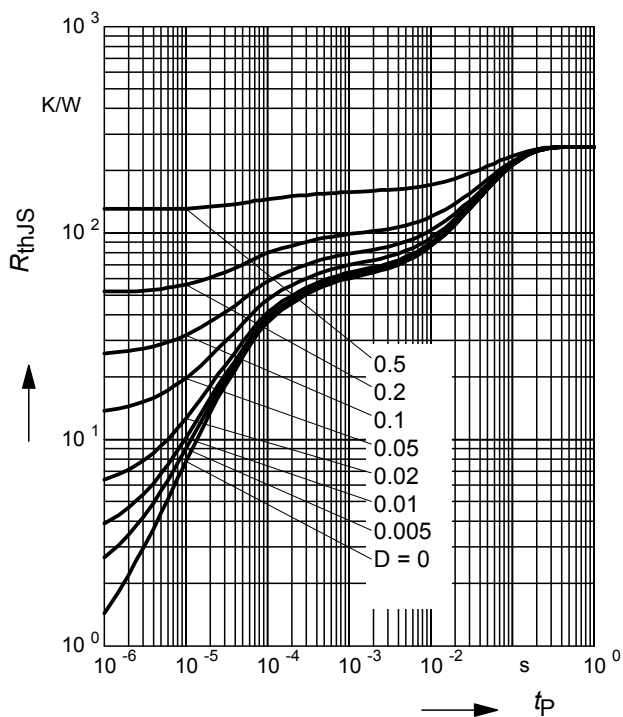
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV70



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

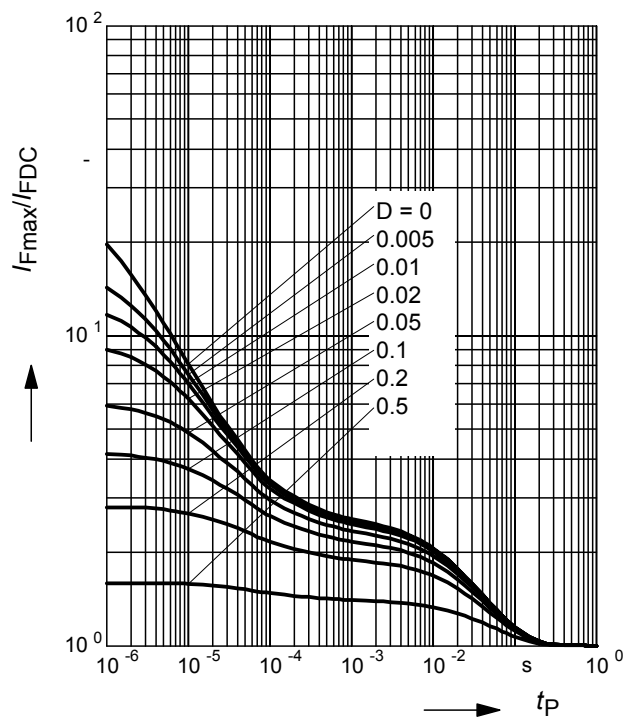
BAV70S



**Permissible Pulse Load**

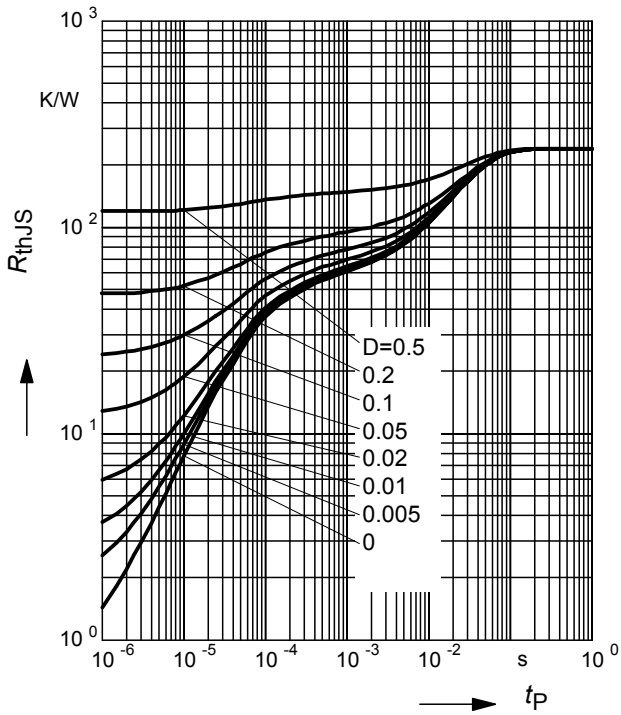
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV70S



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

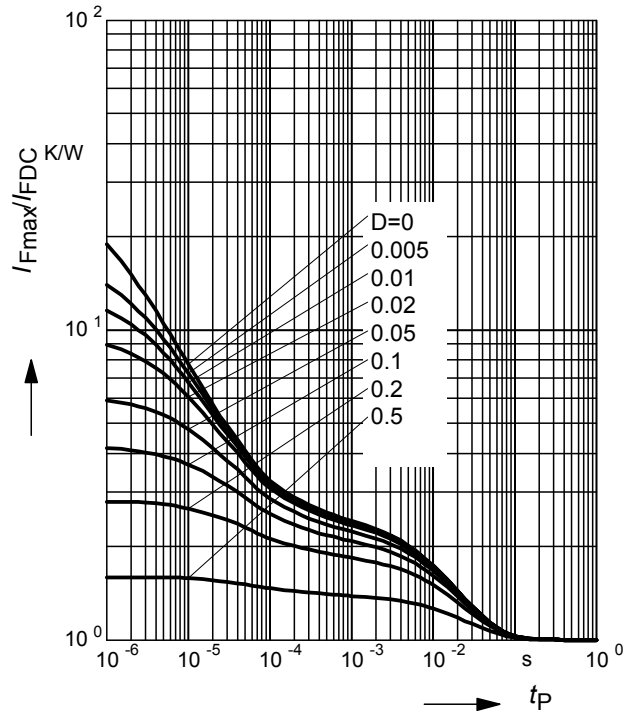
BAV70U



**Permissible Pulse Load**

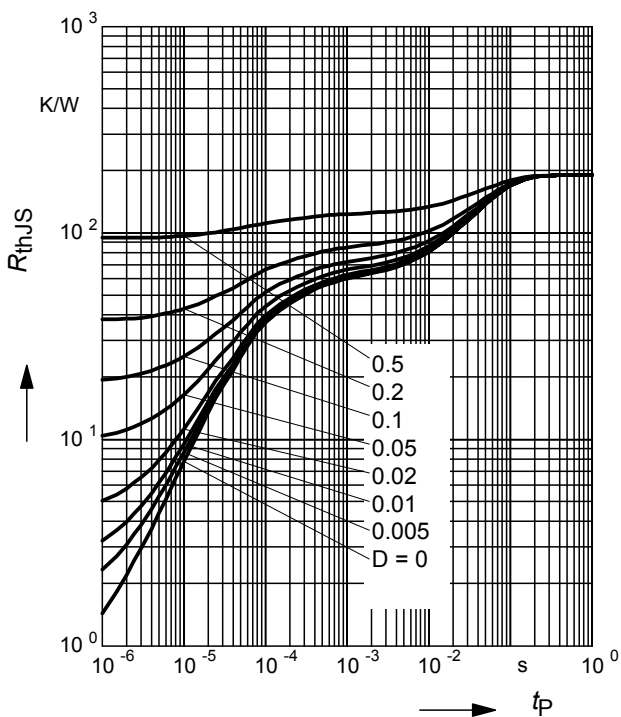
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV70U



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

BAV70W



**Permissible Pulse Load**

$I_{Fmax} / I_{FDC} = f(t_p)$

BAV70W

